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#### What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

#### Applications of "<u>Embedded -</u> <u>Microcontrollers</u>"

#### Details

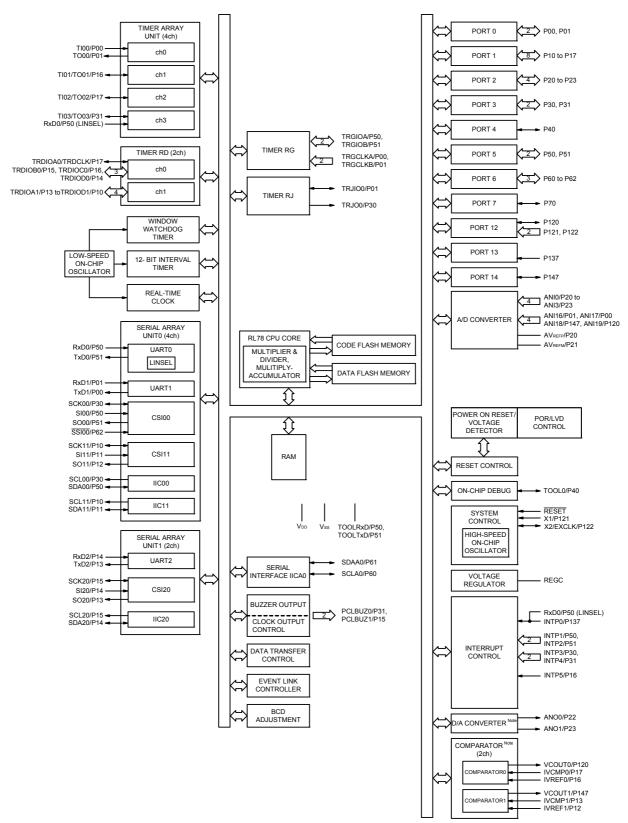
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Details	
Product Status	Active
Core Processor	RL78
Core Size	16-Bit
Speed	32MHz
Connectivity	CSI, I <sup>2</sup> C, LINbus, UART/USART
Peripherals	DMA, LVD, POR, PWM, WDT
Number of I/O	48
Program Memory Size	64KB (64K x 8)
Program Memory Type	FLASH
EEPROM Size	4K x 8
RAM Size	5.5K x 8
Voltage - Supply (Vcc/Vdd)	1.6V ~ 5.5V
Data Converters	A/D 12x8/10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 85°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LQFP
Supplier Device Package	64-LFQFP (10x10)
Purchase URL	https://www.e-xfl.com/product-detail/renesas-electronics-america/r5f104leafb-30

Email: info@E-XFL.COM

Address: Room A, 16/F, Full Win Commercial Centre, 573 Nathan Road, Mongkok, Hong Kong

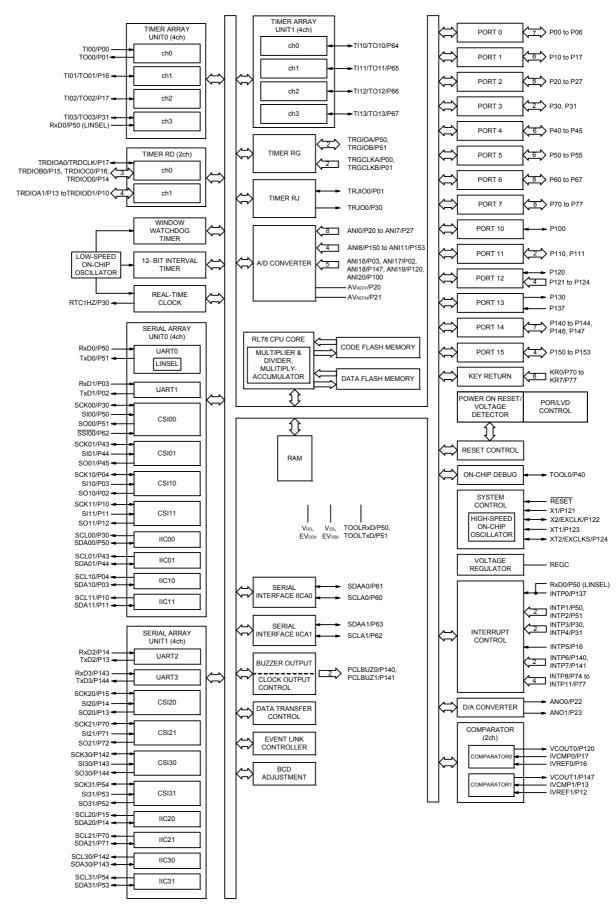
### 1.5.2 32-pin products



**Note** Mounted on the 96 KB or more code flash memory products.



### 1.5.9 80-pin products





[30-pin, 32-pin, 36-pin, 40-pin products (code flash memory 96 KB to 256 KB)]

# Caution This outline describes the functions at the time when Peripheral I/O redirection register 0, 1 (PIOR0, 1) are set to 00H.

	(PIORU, 1) are set to				(1/2)		
		30-pin	32-pin	36-pin	40-pin		
	Item	R5F104Ax (x = F, G)	R5F104Bx (x = F, G)	R5F104Cx (x = F, G)	R5F104Ex (x = F to H)		
Code flash mer	mory (KB)	96 to 128	96 to 128	96 to 128	96 to 192		
Data flash men	nory (KB)	8	8	8	8		
RAM (KB)							
Address space		1 MB					
Main system clock	High-speed system clock	HS (high-speed main) mo HS (high-speed main) mo LS (low-speed main) mod	ation, external main system de: 1 to 20 MHz (Vpp = 2 de: 1 to 16 MHz (Vpp = 2 e: 1 to 8 MHz (Vpp = 1. de: 1 to 4 MHz (Vpp = 1.	2.7 to 5.5 V), 2.4 to 5.5 V), 3 to 5.5 V),			
	High-speed on-chip oscillator clock (fiH)	HS (high-speed main) mod	<ul> <li>de: 1 to 32 MHz (VDD = 2</li> <li>de: 1 to 16 MHz (VDD = 2</li> <li>e: 1 to 8 MHz (VDD = 1.6</li> <li>de: 1 to 4 MHz (VDD = 1.6</li> </ul>	.4 to 5.5 V), 8 to 5.5 V),			
Subsystem clo	ck		_		XT1 (crystal) oscillation, external subsystem clock input (EXCLKS) 32.768 kHz		
Low-speed on-	chip oscillator clock	15 kHz (TYP.): VDD = 1.6	to 5.5 V				
General-purpos	se register	8 bits $\times$ 32 registers (8 bits $\times$ 8 registers $\times$ 4 banks)					
Minimum instru	iction execution time	$0.03125\mu s$ (High-speed of	on-chip oscillator clock: fін	= 32 MHz operation)			
		0.05 µs (High-speed syste	em clock: fmx = 20 MHz op	eration)			
			_		30.5 μs (Subsystem clock: fsue = 32.768 kHz operation)		
Instruction set		Multiplication and Accur		+ 32 bits)	,		
I/O port	Total	26	28	32	36		
	CMOS I/O	21	22	26	28		
	CMOS input	3	3	3	5		
	CMOS output	_	_	_	-		
	N-ch open-drain I/O (6 V tolerance)	2	3	3	3		
Timer	16-bit timer	8 channels (TAU: 4 channels, Timer F	RJ: 1 channel, Timer RD: 2	channels, Timer RG: 1 c	hannel)		
	Watchdog timer	1 channel					
	Real-time clock (RTC)	1 channel					
	12-bit interval timer	1 channel					
	Timer output	Timer outputs: 13 channe PWM outputs: 9 channels					
	RTC output		_		1 • 1 Hz (subsystem clock: fs⊍B = 32.768 kHz)		

(Note is listed on the next page.)



### 2.3.2 Supply current characteristics

#### (1) Flash ROM: 16 to 64 KB of 30- to 64-pin products

Parameter	Symbol			Conditions			MIN.	TYP.	MAX.	Unit
Supply	IDD1	Operat-	HS (high-speed main)	fносо = 64 MHz,	Basic	V <sub>DD</sub> = 5.0 V		2.4		mA
current		ing mode	mode Note 5	fiH = 32 MHz Note 3	operation	VDD = 3.0 V		2.4		
Note 1				fносо = 32 MHz,	Basic	VDD = 5.0 V		2.1		
				fiH = 32 MHz Note 3	operation	VDD = 3.0 V		2.1		
			HS (high-speed main)	fносо = 64 MHz,	Normal	VDD = 5.0 V		5.1	8.7	mA
			mode Note 5	fiн = 32 MHz Note 3	operation	VDD = 3.0 V		5.1	8.7	
				fносо = 32 MHz,	Normal	VDD = 5.0 V		4.8	8.1	
				fiH = 32 MHz Note 3	operation	VDD = 3.0 V		4.8	8.1	
				fносо = 48 MHz,	Normal	VDD = 5.0 V		4.0	6.9	
				fiH = 24 MHz Note 3	operation	VDD = 3.0 V		4.0	6.9	
				fносо = 24 MHz,	Normal	VDD = 5.0 V		3.8	6.3	
				fiH = 24 MHz Note 3	operation	VDD = 3.0 V		3.8	6.3	
	fносо = 16 MHz, Normal	Normal	VDD = 5.0 V		2.8	4.6				
				fiH = 16 MHz Note 3	operation	VDD = 3.0 V		2.8	4.6	
			LS (low-speed main)	fносо = 8 MHz,	Normal	VDD = 3.0 V		1.3	2.0	mA
			mode <sup>Note 5</sup> LV (low-voltage main)	fiн = 8 MHz Note 3	operation	VDD = 2.0 V		1.3	2.0	
				fносо = 4 MHz,	Normal	VDD = 3.0 V		1.3	1.8	mA
	mode Note 5	fiH = 4 MHz Note 3	operation	VDD = 2.0 V		1.3	1.8			
	HS (high-speed main)	f <sub>MX</sub> = 20 MHz <sup>Note 2</sup> , V <sub>DD</sub> = 5.0 V	Normal	Square wave input		3.3	5.3	mA		
	mode Note 5		operation	Resonator connection		3.4	5.5			
			f <sub>MX</sub> = 20 MHz Note 2,	Normal	Square wave input		3.3	5.3		
				V <sub>DD</sub> = 3.0 V	operation	Resonator connection		3.4	5.5	
					Normal	Square wave input		2.0	3.1	
					operation	Resonator connection		2.1	3.2	
				fmx = 10 MHz Note 2,	Normal	Square wave input		2.0	3.1	1
			VDD = 3.0 V	operation	Resonator connection		2.1	3.2	-	
			LS (low-speed main)	f <sub>MX</sub> = 8 MHz Note 2,	Normal	Square wave input		1.2	1.9	mA
		mode Note 5	VDD = 3.0 V	operation	Resonator connection		1.2	2.0		
				fmx = 8 MHz Note 2,	Normal	Square wave input		1.2	1.9	1
				VDD = 2.0 V	operation	Resonator connection		1.2	2.0	
			Subsystem clock	fsue = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	μA
			operation	TA = -40°C	operation	Resonator connection		4.7	6.1	
				fsue = 32.768 kHz Note 4	Normal	Square wave input		4.7	6.1	1
			TA = +25°C	operation	Resonator connection		4.7	6.1	1	
		fsue = 32.768 kHz Note 4	Normal	Square wave input		4.8	6.7	1		
			TA = +50°C	operation	Resonator connection	1	4.8	6.7	1	
				fsue = 32.768 kHz Note 4	Normal	Square wave input		4.8	7.5	1
				TA = +70°C	operation	Resonator connection		4.8	7.5	1
				fsue = 32.768 kHz Note 4	Normal	Square wave input		5.4	8.9	1
				TA = +85°C	operation	Resonator connection		5.4	8.9	1

(Notes and Remarks are listed on the next page.)

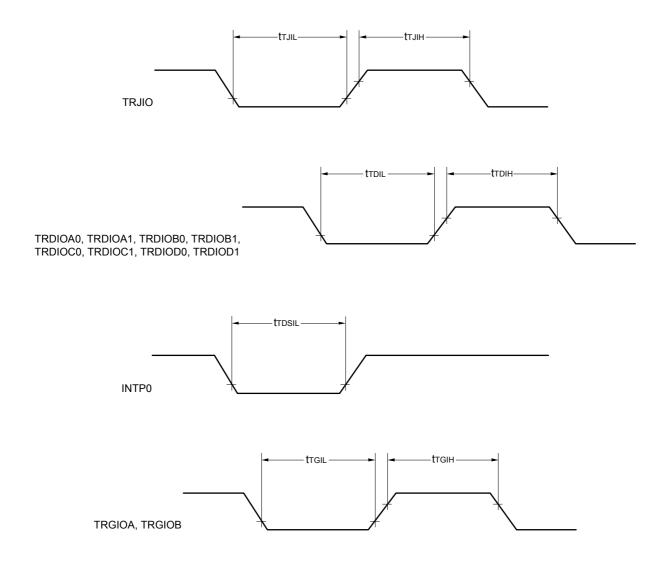
- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- Note 3. When high-speed system clock and subsystem clock are stopped.
- Note 4. When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer
- Note 5. Relationship between operation voltage width, operation frequency of CPU and operation mode is as below.

HS (high-speed main) mode:	$2.7~V \leq V_{DD} \leq 5.5~V@1~MHz$ to 32 MHz
	2.4 V $\leq$ VDD $\leq$ 5.5 V@1 MHz to 16 MHz
LS (low-speed main) mode:	1.8 V $\leq$ VDD $\leq$ 5.5 V@1 MHz to 8 MHz
LV (low-voltage main) mode:	1.6 V $\leq$ VDD $\leq$ 5.5 V@1 MHz to 4 MHz

- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHOCO: High-speed on-chip oscillator clock frequency (64 MHz max.) Remark 3. file:
- High-speed on-chip oscillator clock frequency (32 MHz max.) Remark 4. fsub: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C

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Parameter	Symbol	Conditions	Conditions HS (high-speed main) LS (low-speed main) mode mode		nain)	in) LV (low-voltage main) mode			
			MIN.	MAX.	MIN.	MAX.	MIN.	MAX.	
Data setup time (reception)	tsu: dat	$\begin{array}{l} 2.7 \ \text{V} \leq E V_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	1/f <sub>MCK</sub> + 85 Note 2		1/fмск + 145 Note 2		1/fmck + 145 Note 2		ns
		$\begin{array}{l} 1.8 \text{ V} \leq EV_{\text{DD0}} \leq 5.5 \text{ V}, \\ \text{Cb} = 100 \text{ pF}, \text{ Rb} = 3 \text{ k}\Omega \end{array}$	1/fмск + 145 Note 2		1/fмск + 145 Note 2		1/fmck + 145 Note 2		ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{\mbox{DD0}} < 2.7 \mbox{ V}, \\ C_b \mbox{ = 100 pF}, \mbox{ R}_b \mbox{ = 5 }     \end{array}$	1/fмск + 230 Note 2		1/fмск + 230 Note 2		1/fMCK + 230 Note 2		ns
		$\label{eq:linear} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_{\mbox{b}} = 100 \mbox{ pF}, \mbox{ R}_{\mbox{b}} = 5  k\Omega \end{array}$	1/fмск + 290 Note 2		1/fмск + 290 Note 2		1/fMCK + 290 Note 2		ns
		$\label{eq:linear} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{DD0} < 1.8 \mbox{ V}, \\ C_b \mbox{ = 100 pF, } R_b \mbox{ = 5 } k\Omega \end{array}$	_		1/fмск + 290 Note 2		1/fMCK + 290 Note 2		ns
Data hold time (transmission)	thd: dat	$\begin{array}{l} 2.7 \ \text{V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	0	305	0	305	0	305	ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{DD0} \leq 5.5 \mbox{ V}, \\ C_b = 100 \mbox{ pF}, \mbox{ R}_b = 3 \mbox{ k}\Omega \end{array}$	0	355	0	355	0	355	ns
		$\label{eq:linear} \begin{array}{l} 1.8 \mbox{ V} \leq EV_{DD0} < 2.7 \mbox{ V}, \\ C_b = 100 \mbox{ pF}, \mbox{ R}_b = 5 \mbox{ k}\Omega \end{array}$	0	405	0	405	0	405	ns
		$\label{eq:linear} \begin{array}{l} 1.7 \mbox{ V} \leq EV_{DD0} < 1.8 \mbox{ V}, \\ C_b = 100 \mbox{ pF}, \mbox{ R}_b = 5 \mbox{ k}\Omega \end{array}$	0	405	0	405	0	405	ns
		$\label{eq:linear} \begin{array}{l} 1.6 \mbox{ V} \leq EV_{\mbox{DD0}} < 1.8 \mbox{ V}, \\ C_b \mbox{ = 100 pF, } R_b \mbox{ = 5 } k\Omega \end{array}$	_		0	405	0	405	ns

#### (5) During communication at same potential (simplified I<sup>2</sup>C mode)

#### (TA = -40 to +85°C, 1.6 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(2/2)

**Note 1.** The value must also be equal to or less than fMCK/4.

Note 2. Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(**Remarks** are listed on the next page.)



## (8) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	Conditions		bol Conditions HS (high-speed main) mode			LS (low-speed mode		LV (low-voltage main) mode		Unit
				MIN.	MAX.	MIN.	MAX.	MIN.	MAX.		
SCKp cycle time	<b>t</b> КСҮ1	tксү1 ≥ 4/fc∟к		300		1150		1150		ns	
			$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$	500		1150		1150		ns	
				1150		1150		1150		ns	
SCKp high-level tkr width	tкнı	tkh1 $4.0 V \le EV_{DDC}$ 2.7 V $\le V_b \le 4$ Cb = 30 pF, R	.0 V,	tксү1/2 - 75		tксү1/2 - 75		tксү1/2 - 75		ns	
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \\ \hline 1.8 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \ ^{Note}, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$		tксү1/2 - 170		tксү1/2 - 170		tксү1/2 - 170		ns	
				tксү1/2 - 458		tксү1/2 - 458		tксү1/2 - 458		ns	
SCKp low-level width	tĸ∟1	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$		tксү1/2 - 12		tксү1/2 - 50		tксү1/2 - 50		ns	
2.3 Cb 1.8 1.6	$2.3~V \leq V_b \leq 2$	2.7 V $\leq$ EV <sub>DD0</sub> < 4.0 V, 2.3 V $\leq$ V <sub>b</sub> $\leq$ 2.7 V, C <sub>b</sub> = 30 pF, R <sub>b</sub> = 2.7 k $\Omega$			tксү1/2 - 50		tксү1/2 - 50		ns		
		$\begin{array}{l} 1.8 \ V \leq EV_{DD0} \\ 1.6 \ V \leq V_b \leq 2. \\ C_b = 30 \ pF, \ R_b \end{array}$	0 V <sup>Note</sup> ,	tксү1/2 - 50		tксү1/2 - 50		tксү1/2 - 50		ns	

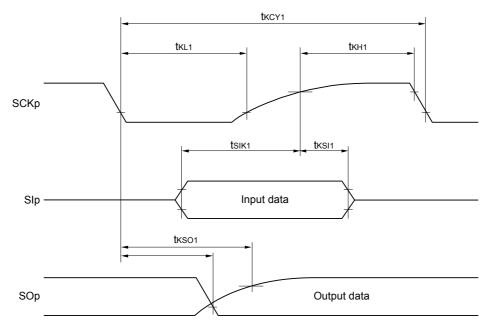
(TA = -40 to +85°C, 1.8 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

**Note** Use it with  $EVDD0 \ge Vb$ .

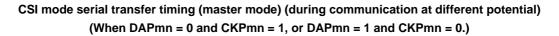
(Remarks are listed two pages after the next page.)

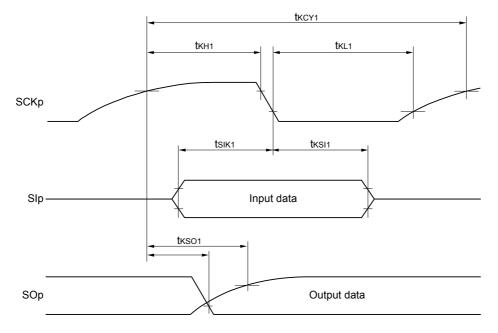


Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.



CSI mode serial transfer timing (master mode) (during communication at different potential) (When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.)



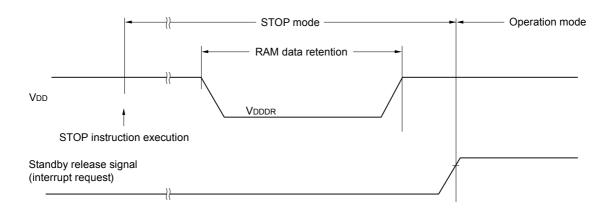


- Remark 1. p: CSI number (p = 00, 01, 10, 20, 30, 31), m: Unit number (m = 0, 1), n: Channel number (n = 0 to 3), g: PIM and POM number (g = 0, 1, 3 to 5, 14)
- Remark 2. CSI01 of 48-, 52-, 64-pin products, and CSI11 and CSI21 cannot communicate at different potential. Use other CSI for communication at different potential.

#### 2.7 **RAM Data Retention Characteristics**

(TA = -40 to +85°C, Vss = 0V)									
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit			
Data retention supply voltage	VDDDR		1.46 Note		5.5	V			

The value depends on the POR detection voltage. When the voltage drops, the RAM data is retained before a POR reset Note is effected, but RAM data is not retained when a POR reset is effected.



#### 2.8 **Flash Memory Programming Characteristics**

$(T_A = -40 \text{ to } +85^{\circ}C, 1.8 \text{ V} \le \text{VDD} \le 5.5 \text{ V}, \text{Vss} = 0 \text{ V})$
--

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
System clock frequency	fclk	$1.8 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	1		32	MHz
Number of code flash rewrites Notes 1, 2, 3	Cerwr	Retained for 20 years TA = 85°C	1,000			Times
Number of data flash rewrites Notes 1, 2, 3		Retained for 1 year TA = 25°C		1,000,000		
		Retained for 5 years TA = 85°C	100,000			
		Retained for 20 years TA = 85°C	10,000			

Note 1. 1 erase + 1 write after the erase is regarded as 1 rewrite. The retaining years are until next rewrite after the rewrite.

Note 2. When using flash memory programmer and Renesas Electronics self-programming library

Note 3. These are the characteristics of the flash memory and the results obtained from reliability testing by Renesas Electronics Corporation.

#### 2.9 **Dedicated Flash Memory Programmer Communication (UART)**

#### (TA = -40 to +85°C, 1.8 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		During serial programming	115,200		1,000,000	bps



### 3.1 Absolute Maximum Ratings

#### Absolute Maximum Ratings

Parameter	Symbols	Conditions	Ratings	Unit
Supply voltage	Vdd		-0.5 to +6.5	V
	EVDD0, EVDD1	EVDD0 = EVDD1	-0.5 to +6.5	V
	EVsso, EVss1	EVsso = EVss1	-0.5 to +0.3	V
REGC pin input voltage	VIREGC	REGC	-0.3 to +2.8	V
			and -0.3 to V_DD +0.3 $^{\text{Note 1}}$	
Input voltage	VI1	P00 to P06, P10 to P17, P30, P31,	-0.3 to EVDD0 +0.3	V
		P40 to P47, P50 to P57, P64 to P67,	and -0.3 to VDD +0.3 Note 2	
		P70 to P77, P80 to P87, P100 to P102,		
		P110, P111, P120, P140 to P147		
	VI2	P60 to P63 (N-ch open-drain)	-0.3 to +6.5	V
	Vı3	P20 to P27, P121 to P124, P137,	-0.3 to V <sub>DD</sub> +0.3 Note 2	V
		P150 to P156, EXCLK, EXCLKS, RESET		
Output voltage	V01	P00 to P06, P10 to P17, P30, P31,	-0.3 to EVDD0 +0.3	V
		P40 to P47, P50 to P57, P60 to P67,	and -0.3 to VDD +0.3 Note 2	
		P70 to P77, P80 to P87, P100 to P102,		
		P110, P111, P120, P130, P140 to P147		
	V02	P20 to P27, P150 to P156	-0.3 to VDD +0.3 Note 2	V
Analog input voltage	VAI1	ANI16 to ANI20	-0.3 to EVDD0 +0.3	
			and -0.3 to AVREF(+) +0.3 Notes 2, 3	V
	VAI2	ANI0 to ANI14	-0.3 to VDD +0.3	v
			and -0.3 to AVREF(+) +0.3 Notes 2, 3	v

Note 1. Connect the REGC pin to Vss via a capacitor (0.47 to 1 μF). This value regulates the absolute maximum rating of the REGC pin. Do not use this pin with voltage applied to it.

Note 2. Must be 6.5 V or lower.

**Note 3.** Do not exceed AVREF (+) + 0.3 V in case of A/D conversion target pin.

- Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.
- Remark 1. Unless specified otherwise, the characteristics of alternate-function pins are the same as those of the port pins.

**Remark 2.** AVREF (+): + side reference voltage of the A/D converter.

Remark 3. Vss: Reference voltage



(1/2)

- Note 1. Total current flowing into VDD and EVDD0, including the input leakage current flowing when the level of the input pin is fixed to VDD, EVDD0 or Vss, EVss0. The values below the MAX. column include the peripheral operation current. However, not including the current flowing into the A/D converter, LVD circuit, I/O port, and on-chip pull-up/pull-down resistors and the current flowing during data flash rewrite.
- Note 2. When high-speed on-chip oscillator and subsystem clock are stopped.
- **Note 3.** When high-speed system clock and subsystem clock are stopped.
- **Note 4.** When high-speed on-chip oscillator and high-speed system clock are stopped. When AMPHS1 = 1 (Ultra-low power consumption oscillation). However, not including the current flowing into the RTC, 12-bit interval timer, and watchdog timer.
- **Note 5.** Relationship between operation voltage width, operation frequency of CPU and operation mode is as below. HS (high-speed main) mode:  $2.7 \text{ V} \le \text{V}_{DD} \le 5.5 \text{ V}_{@}1 \text{ MHz}$  to 32 MHz
  - 2.4 V  $\leq$  VDD  $\leq$  5.5 V@1 MHz to 16 MHz
- Remark 1. fmx: High-speed system clock frequency (X1 clock oscillation frequency or external main system clock frequency)
- Remark 2. fHoco: High-speed on-chip oscillator clock frequency (64 MHz max.)
- Remark 3. fin: High-speed on-chip oscillator clock frequency (32 MHz max.)
- **Remark 4.** fsuB: Subsystem clock frequency (XT1 clock oscillation frequency)
- Remark 5. Except subsystem clock operation, temperature condition of the TYP. value is TA = 25°C



#### Parameter Symbo Conditions MIN. TYP. MAX. fносо = 64 MHz, $V_{DD} = 5.0 V$ 2.6 Supply DD1 Operat-HS (high-speed main) Basic current ing mode mode Note 5 fill = 32 MHz Note 3 operation VDD = 3.0 V 2.6 Note 1 fносо = 32 MHz. Basic VDD = 5.0 V 2.3 fiH = 32 MHz Note 3 operation VDD = 3.0 V 2.3 fносо = 64 MHz, VDD = 5.0 V HS (high-speed main) Normal 5.4 10.9 mode Note 5 fiH = 32 MHz Note 3 operation $V_{DD} = 3.0 V$ 54 10.9 VDD = 5.0 V 10.3 fносо = 32 MHz. Normal 5.0 fin = 32 MHz Note 3 operation VDD = 3.0 V 10.3 5.0 VDD = 5.0 V fHOCO = 48 MHz. 42 82 Normal fiH = 24 MHz Note 3 operation VDD = 3.0 V 4.2 8.2 fносо = 24 MHz, Normal VDD = 5.0 V 4.0 7.8 fill = 24 MHz Note 3 operation VDD = 3.0 V 40 78 fносо = 16 MHz, Normal VDD = 5.0 V 3.0 5.6 fin = 16 MHz Note 3 operation VDD = 3.0 V 3.0 5.6 HS (high-speed main) 3.4 f<sub>MX</sub> = 20 MHz Note 2 Normal Square wave input 6.6 mode Note 5 VDD = 5.0 V operation Resonator connection 3.6 6.7 f<sub>MX</sub> = 20 MHz Note 2, Normal Square wave input 34 6.6 operation $V_{DD} = 3.0 V$ Resonator connection 3.6 6.7 fmx = 10 MHz Note 2, 2.1 3.9 Normal Square wave input VDD = 5.0 V operation Resonator connection 22 4.0 f<sub>MX</sub> = 10 MHz Note 2. Normal Square wave input 2.1 3.9 VDD = 3.0 V operation Resonator connection 2.2 4.0 fsub = 32.768 kHz Note 4 49 71 Subsystem clock Normal Square wave input operation operation $T_A = -40^{\circ}C$ Resonator connection 4.9 7.1 fsub = 32.768 kHz Note 4 Normal Square wave input 4.9 7.1 $T_A = +25^{\circ}C$ operation 4.9 7.1 Resonator connection Normal 5.1 8.8 fsub = 32.768 kHz Note 4 Square wave input $T_A = +50^{\circ}C$ operation 8.8 Resonator connection 5.1 10.5 fsub = 32.768 kHz Note 4 Square wave input 5.5 Normal TA = +70°C operation Resonator connection 5.5 10.5 fsub = 32.768 kHz Note 4 Normal 6.5 14.5 Square wave input TA = +85°C operation 6.5 14.5 Resonator connection fsub = 32.768 kHz Note 4 Normal Square wave input 13.0 58.0

 $T_{A} = +105^{\circ}C$ 

#### (2) Flash ROM: 96 to 256 KB of 30- to 100-pin products

#### (TA = -40 to +105°C, 2.4 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(Notes and Remarks are listed on the next page.)

operation

Resonator connection

Unit

mΑ

mΑ

mΑ

μΑ

13.0

58.0

#### (4) During communication at same potential (simplified I<sup>2</sup>C mode)

(TA = -40 to +105°C, 2.4 V $\leq$ EV	$VDD0 = EVDD1 \le VDD$	≤ 5.5 V, Vss = EVss₀ = EVss₁ = 0 V)

Parameter	Symbol	Conditions	HS (high-speed	main) mode	Unit
			MIN.	MAX.	
SCLr clock frequency	fsc∟	$\begin{array}{l} 2.7 \ \text{V} \leq E V_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$		400 Note 1	kHz
		$\begin{array}{l} 2.4 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ C_{b} \texttt{=} 100 \ pF, \ R_{b} \texttt{=} 3 \ k\Omega \end{array}$		100 Note 1	kHz
Hold time when SCLr = "L"	tLOW	$\begin{array}{l} 2.7 \ \text{V} \leq E V_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	1200		ns
		$\begin{array}{l} 2.4V \leq EV_{DD0} \leq 5.5 \; V, \\ C_{b} = 100 \; pF, \; R_{b} = 3 \; k\Omega \end{array}$	4600		ns
Hold time when SCLr = "H"	tніgн	$\begin{array}{l} 2.7 \ \text{V} \leq E V_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	1200		ns
		$2.4 \text{ V} \leq \text{EV}_{\text{DD0}} \leq 5.5 \text{ V},$ Cb = 100 pF, Rb = 3 k $\Omega$	4600		ns
Data setup time (reception)	tsu: dat	$\begin{array}{l} 2.7 \ \text{V} \leq E V_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	1/f <sub>MCK</sub> + 220 Note 2		ns
		$\begin{array}{l} 2.4V \leq EV_{DD0} \leq 5.5 \; V, \\ C_{b} = 100 \; pF, \; R_{b} = 3 \; k\Omega \end{array}$	1/fMCK + 580 Note 2		ns
Data hold time (transmission)	thd: dat	$\begin{array}{l} 2.7 \ \text{V} \leq E V_{\text{DD0}} \leq 5.5 \ \text{V}, \\ \text{C}_{\text{b}} = 50 \ \text{pF}, \ \text{R}_{\text{b}} = 2.7 \ \text{k}\Omega \end{array}$	0	770	ns
		$\begin{array}{l} 2.4 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ C_{b} \texttt{=} 100 \ pF, \ R_{b} \texttt{=} 3 \ k\Omega \end{array}$	0	1420	ns

**Note 1.** The value must also be equal to or less than fMCK/4.

**Note 2.** Set the fMCK value to keep the hold time of SCLr = "L" and SCLr = "H".

Caution Select the normal input buffer and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SDAr pin and the normal output mode for the SCLr pin by using port input mode register g (PIMg) and port output mode register h (POMh).

(**Remarks** are listed on the next page.)



#### (5) Communication at different potential (1.8 V, 2.5 V, 3 V) (UART mode)

#### (TA = -40 to +105°C, 2.4 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

(1/2)

Parameter	Symbol	Conditions		HS (high-speed main) mode		Unit
				MIN.	MAX.	
Transfer rate reception		reception	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V \end{array}$		fмск/12 Note 1	bps
			Theoretical value of the maximum transfer rate $f_{MCK}$ = $f_{CLK}$ Note 3		2.6	Mbps
			$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V \end{array}$		fмск/12 Note 1	bps
			Theoretical value of the maximum transfer rate fmck = fclk Note 3		2.6	Mbps
			$\begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V \end{array}$		f <sub>MCK</sub> /12 Notes 1, 2	bps
			Theoretical value of the maximum transfer rate $f_{MCK}$ = $f_{CLK}$ $^{Note\ 3}$		2.6	Mbps

**Note 1.** Transfer rate in the SNOOZE mode is 4800 bps only.

However, the SNOOZE mode cannot be used when FRQSEL4 = 1.

```
Note 2. The following conditions are required for low voltage interface when EVDD0 < VDD.
```

 $2.4 \text{ V} \leq \text{EV}_{\text{DD0}} < 2.7 \text{ V}$ : MAX. 1.3 Mbps

- **Note 3.** The maximum operating frequencies of the CPU/peripheral hardware clock (fcLK) are: HS (high-speed main) mode:  $32 \text{ MHz} (2.7 \text{ V} \le \text{VDD} \le 5.5 \text{ V})$ 
  - 16 MHz (2.4 V  $\leq$  VDD  $\leq$  5.5 V)
- Caution Select the TTL input buffer for the RxDq pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the TxDq pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.
- Remark 1. Vb [V]: Communication line voltage
- **Remark 2.** q: UART number (q = 0 to 3), g: PIM and POM number (g = 0, 1, 5, 14)
- Remark 3. fMCK: Serial array unit operation clock frequency

(Operation clock to be set by the CKSmn bit of serial mode register mn (SMRmn). m: Unit number, n: Channel number (mn = 00 to 03, 10 to 13)

**Remark 4.** UART2 cannot communicate at different potential when bit 1 (PIOR01) of peripheral I/O redirection register 0 (PIOR0) is 1.



## (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	Conditions		HS (high-speed main) mode		Unit
				MIN.	MAX.	
SCKp cycle time	tксү1	tксү1 ≥ 4/fclк		600		ns
			$\label{eq:VDD0} \begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_b \leq 2.7 \; V, \\ & C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{split}$	1000		ns
			$\begin{array}{l} 2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ 1.6 \; V \leq V_b \leq 2.0 \; V, \\ C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{array}$	2300		ns
SCKp high-level width	tкнı	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ V, \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \ k\Omega \end{array}$		tĸcy1/2 - 150		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		tксү1/2 - 340		ns
		$\begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$		tксү1/2 - 916		ns
SCKp low-level width	tĸL1	$\begin{array}{l} 4.0 \ V \leq EV_{DD0} \leq 5.5 \ ' \\ 2.7 \ V \leq V_b \leq 4.0 \ V, \\ C_b = 30 \ pF, \ R_b = 1.4 \end{array}$	,	tксү1/2 - 24		ns
		$\begin{array}{l} 2.7 \ V \leq EV_{DD0} < 4.0 \ V, \\ 2.3 \ V \leq V_b \leq 2.7 \ V, \\ C_b = 30 \ pF, \ R_b = 2.7 \ k\Omega \end{array}$		tkcy1/2 - 36		ns
		$\begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \end{array}$	,	tксү1/2 - 100		ns

#### (TA = -40 to +105°C, 2.4 V $\leq$ EVDD0 = EVDD1 $\leq$ VDD $\leq$ 5.5 V, VSS = EVSS0 = EVSS1 = 0 V)

Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(**Remarks** are listed two pages after the next page.)



## (6) Communication at different potential (1.8 V, 2.5 V, 3 V) (CSI mode) (master mode, SCKp... internal clock output)

Parameter	Symbol	Conditions	HS (high-spe	Unit	
			MIN.	MAX.	
SIp setup time (to SCKp↑) <sup>Note</sup>	tsiкı		162		ns
		$\begin{array}{l} 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ 2.3 \; V \leq V_b \leq 2.7 \; V, \\ C_b = 30 \; pF, \; R_b = 2.7 \; k\Omega \end{array}$	354		ns
		$\label{eq:2.4} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$	958		ns
SIp hold time (from SCKp↑) <sup>Note</sup>	tksi1		38		ns
		$\label{eq:VDD0} \begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ & C_{b} = 30 \; pF, \; R_{b} = 2.7 \; k\Omega \end{split}$	38		ns
		$\label{eq:2.4} \begin{split} & 2.4 \; V \leq EV_{DD0} < 3.3 \; V, \\ & 1.6 \; V \leq V_b \leq 2.0 \; V, \\ & C_b = 30 \; pF, \; R_b = 5.5 \; k\Omega \end{split}$	38		ns
Delay time from SCKp↓ to SOp output <sup>Note</sup>	tkso1			200	ns
		$\label{eq:VDD0} \begin{split} & 2.7 \; V \leq EV_{DD0} < 4.0 \; V, \\ & 2.3 \; V \leq V_{b} \leq 2.7 \; V, \\ & C_{b} = 30 \; pF, \; R_{b} = 2.7 \; k\Omega \end{split}$		390	ns
		$\label{eq:VDD0} \begin{array}{l} 2.4 \ V \leq EV_{DD0} < 3.3 \ V, \\ 1.6 \ V \leq V_b \leq 2.0 \ V, \\ C_b = 30 \ pF, \ R_b = 5.5 \ k\Omega \end{array}$		966	ns

**Note** When DAPmn = 0 and CKPmn = 0, or DAPmn = 1 and CKPmn = 1.

(Remarks are listed on the page after the next page.)



Caution Select the TTL input buffer for the SIp pin and the N-ch open drain output (VDD tolerance (for the 30- to 52-pin products)/EVDD tolerance (for the 64- to 100-pin products)) mode for the SOp pin and SCKp pin by using port input mode register g (PIMg) and port output mode register g (POMg). For VIH and VIL, see the DC characteristics with TTL input buffer selected.

(3) When reference voltage (+) = VDD (ADREFP1 = 0, ADREFP0 = 0), reference voltage (-) = Vss (ADREFM = 0), target pin: ANI0 to ANI14, ANI16 to ANI20, internal reference voltage, and temperature sensor output voltage

(TA = -40 to +105°C, 2.4 V  $\leq$  EVDD0 = EVDD1  $\leq$  VDD  $\leq$  5.5 V, Vss = EVss0 = EVss1 = 0 V, Reference voltage (+) = VDD, Reference voltage (-) = Vss)

Parameter	Symbol	Conditions			TYP.	MAX.	Unit
Resolution	RES			8		10	bit
Overall error Note 1	AINL	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$		1.2	±7.0	LSB
Conversion time	tconv	10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.125		39	μs
		Target pin: ANI0 to ANI14, ANI16 to ANI20	$2.7~V \leq V_{DD} \leq 5.5~V$	3.1875		39	μs
			$2.4~V \leq V_{DD} \leq 5.5~V$	17		39	μs
		10-bit resolution	$3.6~V \leq V_{DD} \leq 5.5~V$	2.375		39	μs
		Target pin: internal reference voltage, and temperature sensor output voltage (HS (high-speed main) mode)	$2.7~V \leq V_{DD} \leq 5.5~V$	3.5625		39	μs
			$2.4~\text{V} \leq \text{V}_\text{DD} \leq 5.5~\text{V}$	17		39	μs
Zero-scale error Notes 1, 2	Ezs	10-bit resolution	$2.4~\text{V} \leq \text{V}_\text{DD} \leq 5.5~\text{V}$			±0.60	%FSR
Full-scale error Notes 1, 2	Efs	10-bit resolution	$2.4~V \leq V_{DD} \leq 5.5~V$			±0.60	%FSR
Integral linearity error Note 1	ILE	10-bit resolution	$2.4~\text{V} \leq \text{V}_\text{DD} \leq 5.5~\text{V}$			±4.0	LSB
Differential linearity error Note 1	DLE	10-bit resolution	$2.4~\text{V} \leq \text{V}_{\text{DD}} \leq 5.5~\text{V}$			±2.0	LSB
Analog input voltage	VAIN	ANI0 to ANI14	1	0		Vdd	V
		ANI16 to ANI20		0		EV <sub>DD0</sub>	V
		Internal reference voltage (2.4 V $\leq$ VDD $\leq$ 5.5 V, HS (high-speed main) mode)		V <sub>BGR</sub> Note 3		V	
	Temperature sensor output voltage (2.4 V $\leq$ VpD $\leq$ 5.5 V, HS (high-speed		node)	۲V	MPS25 Not	te 3	V

Note 1. Excludes quantization error (±1/2 LSB).

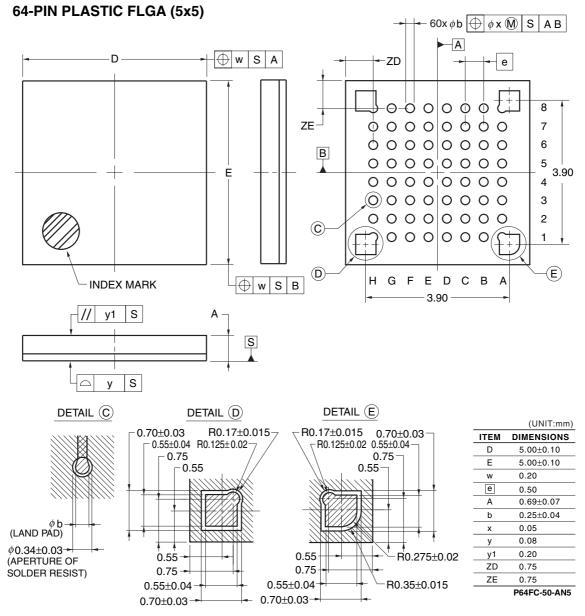
Note 2. This value is indicated as a ratio (% FSR) to the full-scale value.

Note 3. Refer to 3.6.2 Temperature sensor characteristics/internal reference voltage characteristic.



R5F104LCALA, R5F104LDALA, R5F104LEALA, R5F104LFALA, R5F104LGALA, R5F104LHALA, R5F104LJALA R5F104LKALA, R5F104LLALA

R5F104LCGLA,R5F104LDGLA, R5F104LEGLA, R5F104LFGLA, R5F104LGGLA, R5F104LHGLA, R5F104LJGLA R5F104LKGLA, R5F104LLGLA



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REVISION HISTORY RL78/G14 Datasheet
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Rev.	Data		Description			
Rev.	Date Page		Summary			
3.20	Jan 05, 2015	p.135, 137, 139, 141, 143, 145	Modification of specifications in 3.3.2 Supply current characteristics			
		p.197	Modification of part number in 4.7 52-pin products			
3.30	Aug 12, 2016	p.143, 145	Addition of maximum values in (3) Flash ROM: 384 to 512 KB of 48- to 100-pin products of 3.3.2 Supply current characteristics			

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